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(54) **SURFACE ACOUSTIC WAVE DEVICE**

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(71) Applicant: **Murata Manufacturing Co., Ltd.**,
Nagaokakyo-shi, Kyoto-fu (JP)

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(72) Inventors: **Tetsuya Kimura**, Nagaokakyo (JP);
Yasuyuki Ida, Nagaokakyo (JP); **Mari Saji**, Nagaokakyo (JP)

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(73) Assignee: **MURATA MANUFACTURING CO., LTD.**, Kyoto (JP)

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Primary Examiner — J. San Martin

(74) *Attorney, Agent, or Firm* — Keating & Bennett, LLP

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H01L 41/107 (2006.01)

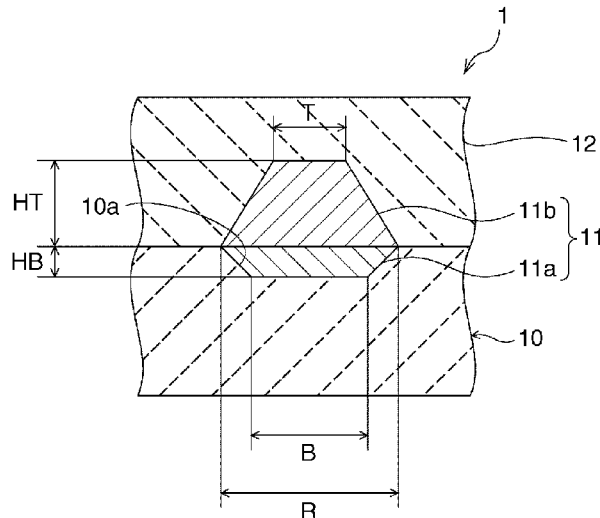
(57) **ABSTRACT**

(52) **U.S. Cl.**
CPC **H01L 41/107** (2013.01); **H03H 9/14541** (2013.01)

A surface acoustic wave device includes a piezoelectric substrate including a groove located in a surface thereof, an IDT electrode, and a dielectric film. The IDT electrode includes a first electrode layer located in the groove and a second electrode layer located outside the groove. The dielectric film is arranged on the piezoelectric substrate so as to cover the IDT electrode. The second electrode layer is tapered toward a side opposite to the piezoelectric substrate.

(58) **Field of Classification Search**
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See application file for complete search history.

5 Claims, 2 Drawing Sheets



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FIG. 1

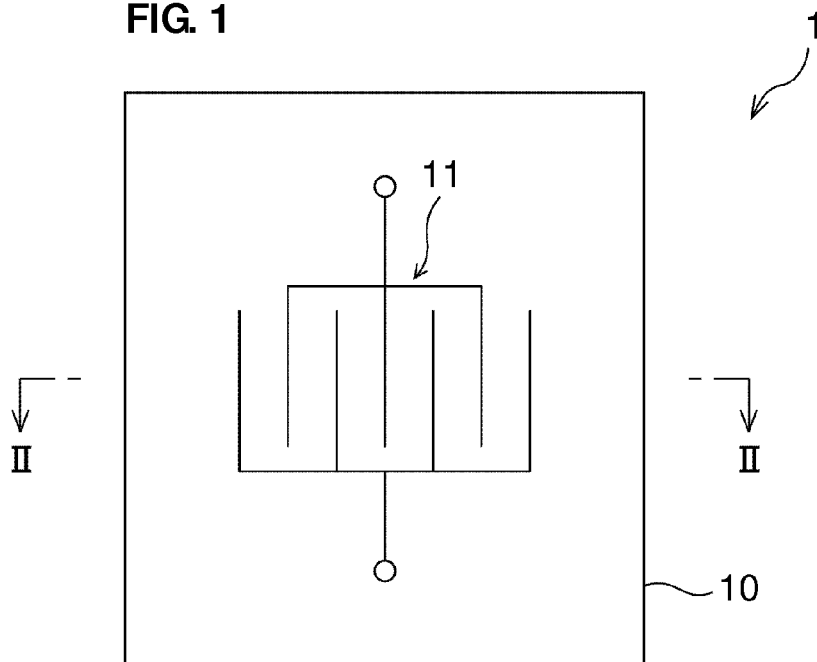


FIG. 2

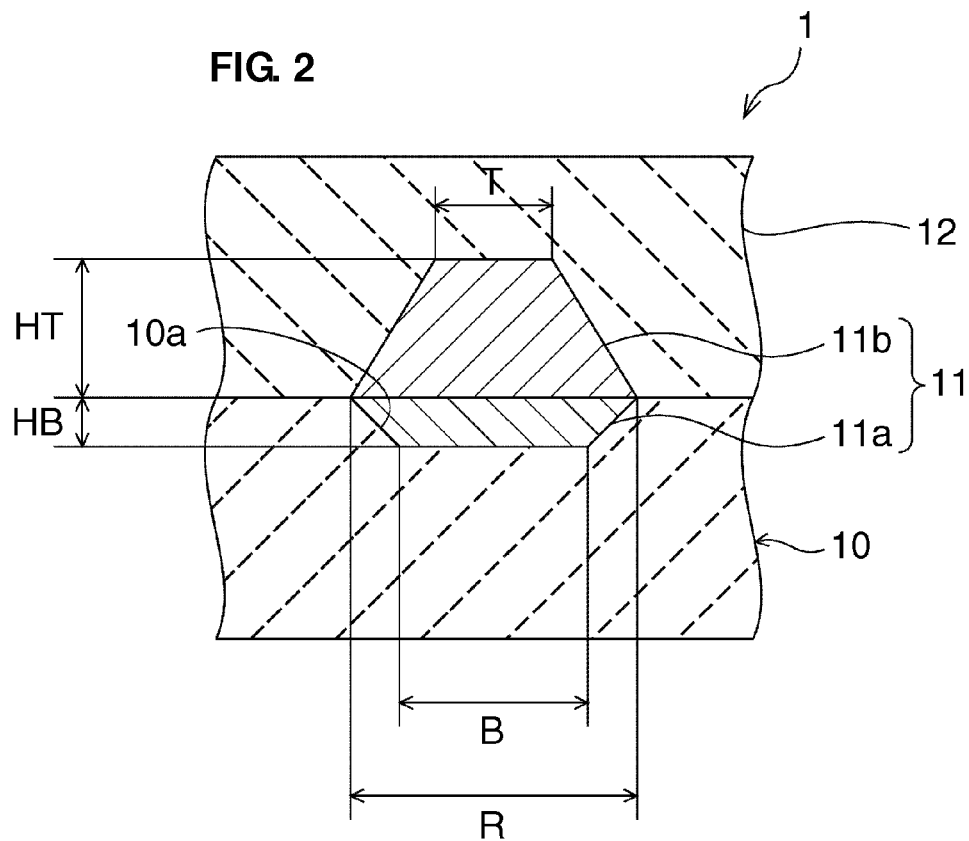


FIG. 3

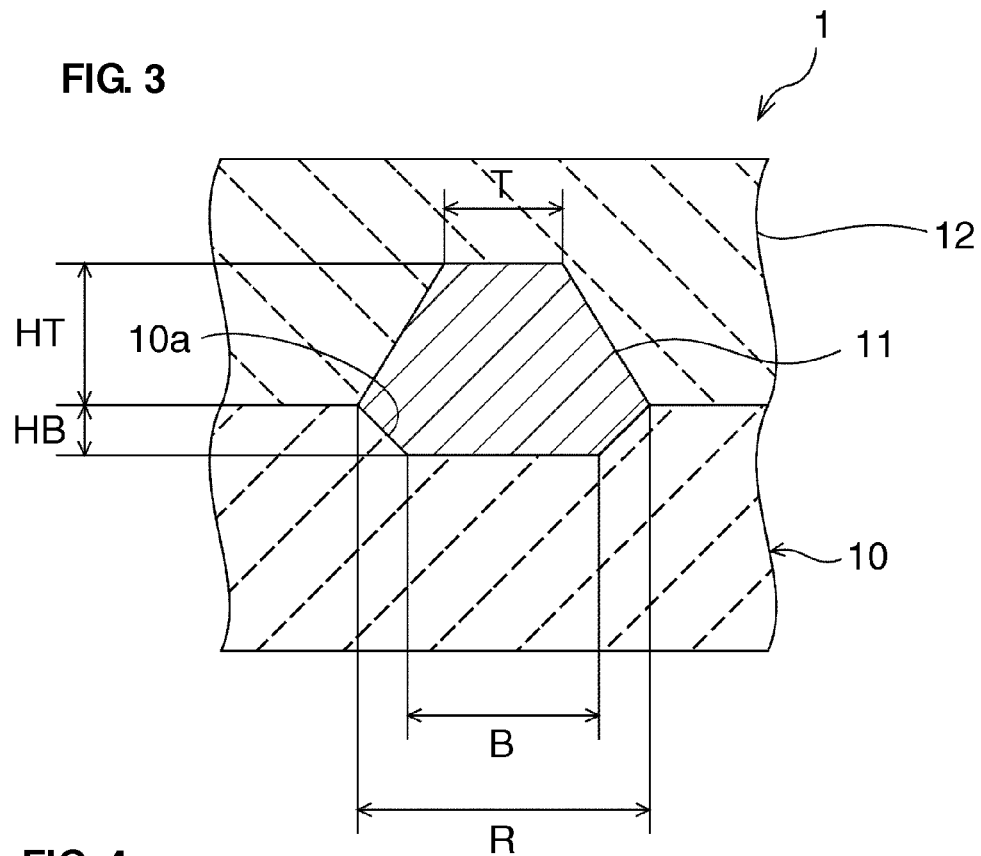
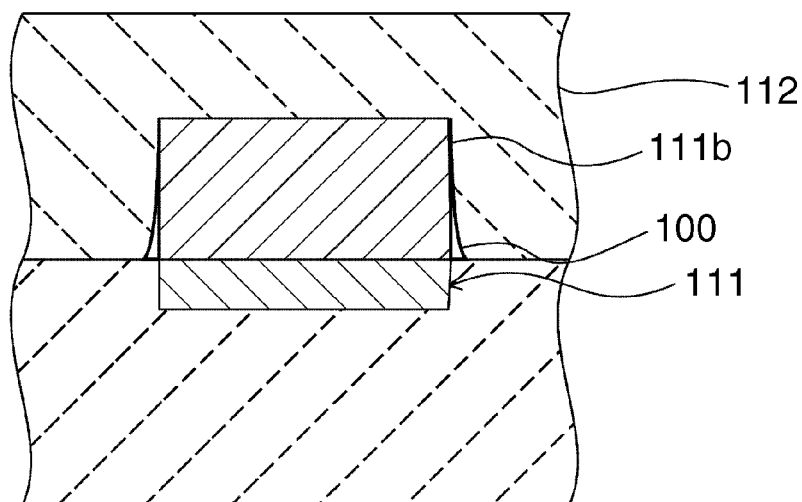


FIG. 4



SURFACE ACOUSTIC WAVE DEVICE

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a surface acoustic wave device. In particular, the present invention relates to a surface acoustic wave device including an IDT electrode of which a portion is embedded in a groove located in a piezoelectric substrate and a dielectric film arranged so as to cover the IDT electrode.

2. Description of the Related Art

In recent years, surface acoustic wave devices such as surface acoustic wave resonators and surface acoustic wave filters which utilize surface acoustic waves have been widely used.

A surface acoustic wave device includes a piezoelectric substrate and an IDT electrode formed on the piezoelectric substrate. In the surface acoustic wave device, an elastic wave excited by the IDT electrode propagates as a surface acoustic wave on the surface of the piezoelectric substrate.

In the surface acoustic wave device, a LiNbO_3 substrate, a LiTaO_3 substrate, or the like is generally used as the piezoelectric substrate. The LiNbO_3 substrate and LiTaO_3 substrate have negative temperature coefficients of frequency (TCF). Thus, when the LiNbO_3 substrate or the LiTaO_3 substrate is used as the piezoelectric substrate, the frequency characteristics of the surface acoustic wave device change with temperature change. In view of this, for example, WO 2010/016192A1 described below states that a portion of an IDT electrode is embedded in a groove formed on a piezoelectric substrate and a SiO_2 film having a positive TCF is further formed so as to cover the IDT electrode, thereby reducing the temperature dependency of the frequency characteristics of a surface acoustic wave device.

In addition, in a surface acoustic wave device, a dielectric film may be formed on a piezoelectric substrate so as to cover an IDT electrode, for the purpose of improving voltage resistance and other purposes unlike improvement of frequency-temperature characteristics as described above.

However, when a dielectric film is formed on a piezoelectric substrate so as to cover an IDT electrode, favorable frequency characteristics may not be obtained.

SUMMARY OF THE INVENTION

Accordingly, preferred embodiments of the present invention improve frequency characteristics such as resonant characteristics and filter characteristics in a surface acoustic wave device which includes a dielectric film arranged on a piezoelectric substrate so as to cover an IDT electrode.

As a result of thorough research, the inventors of the present invention have discovered that the cause for deterioration of frequency characteristics when a dielectric film is formed is that a gap is formed between the dielectric film and an IDT electrode. Preferred embodiments of the present invention were developed based on this discovery.

A surface acoustic wave device according to a preferred embodiment of the present invention includes a piezoelectric substrate, an IDT electrode, and a dielectric film. On a surface of the piezoelectric substrate, a groove is formed. The IDT electrode includes a first electrode layer located in the groove and a second electrode layer located outside the groove. The dielectric film is arranged on the piezoelectric substrate so as to cover the IDT electrode. The second electrode layer is tapered toward a side opposite to the piezoelectric substrate.

In a specific aspect of the surface acoustic wave device according to a preferred embodiment of the present invention, the first electrode layer is tapered toward the piezoelectric substrate side.

In another specific aspect of the surface acoustic wave device according to a preferred embodiment of the present invention, a cross-sectional shape of the second electrode layer is trapezoidal. A ratio (T/R) of a length (T) of an upper base to a length (R) of a lower base in a cross section of the second electrode layer is preferably within a range of about 0.8 to about 0.99, for example. According to this configuration, frequency characteristics such as resonant characteristics and filter characteristics can be further improved.

In a preferred embodiment of the present invention, the “trapezoidal shape” includes a shape in which at least some of an upper base, a lower base, and sides are formed as curves, and a trapezoidal shape in which corners are chamfered or round-chamfered.

In another specific aspect of the surface acoustic wave device according to a preferred embodiment of the present invention, a ratio (HT/R) of a height (HT) to the length (R) of the lower base in the cross section of the second electrode layer preferably is within a range of about 0.1 to about 0.25, for example. According to this configuration, frequency characteristics such as resonant characteristics and filter characteristics can be further improved.

In still another specific aspect of the surface acoustic wave device according to a preferred embodiment of the present invention, the dielectric film is made from silicon oxide or silicon nitride.

In a preferred embodiment of the present invention, the second electrode layer of the IDT electrode which is located outside the groove is tapered toward the side opposite to the piezoelectric substrate. Thus, the occurrence of a gap between the IDT electrode and the dielectric film is prevented. Therefore, scattering of surface acoustic waves and the like can be prevented. In addition, an effect of improving voltage resistance and frequency-temperature characteristics by forming the dielectric film is sufficiently obtained. As a result, high-quality frequency characteristics of the surface acoustic wave device can be achieved.

The above and other elements, features, steps, characteristics and advantages of the present invention will become more apparent from the following detailed description of the preferred embodiments with reference to the attached drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic plan view of a surface acoustic wave device according to a preferred embodiment of the present invention.

FIG. 2 is a schematic cross-sectional view of the surface acoustic wave device according to a preferred embodiment of the present invention.

FIG. 3 is a schematic cross-sectional view of a surface acoustic wave device according to a first modification of a preferred embodiment of the present invention.

FIG. 4 is a schematic cross-sectional view of a surface acoustic wave device according to a comparative example of a preferred embodiment of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

Hereinafter, preferred embodiments of the present invention will be described with, an example, a surface acoustic wave device 1 shown in FIGS. 1 and 2 which preferably is a

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surface acoustic wave resonator. It is noted that the surface acoustic wave device **1** is merely illustrative. The surface acoustic wave device according to the present invention is not limited to the surface acoustic wave device **1** in any way. The surface acoustic wave device according to a preferred embodiment of the present invention may be, for example, a surface acoustic wave filter device.

FIG. **1** is a schematic plan view of the surface acoustic wave device according to the present preferred embodiment. FIG. **2** is a schematic cross-sectional view of the surface acoustic wave device according to the present preferred embodiment. It is noted that in FIG. **1**, drawing of a dielectric film **12** is omitted for convenience of drawing.

As shown in FIGS. **1** and **2**, the surface acoustic wave device **1** includes a piezoelectric substrate **10**. The piezoelectric substrate **10** can be made of an appropriate piezoelectric material. The piezoelectric substrate **10** can be made of, for example, LiNbO₃, LiTaO₃, ZnO, crystal, or the like.

An IDT electrode **11** is located on the piezoelectric substrate **10** and includes a pair of comb electrodes which are inserted into each other. In the surface acoustic wave device **1**, an elastic wave excited by the IDT electrode **11** propagates as a surface acoustic wave on the surface of the piezoelectric substrate **10** such that the function of the surface acoustic wave device **1** is achieved.

The dielectric film **12** is arranged on the piezoelectric substrate **10** so as to cover the IDT electrode **11**. In the present preferred embodiment, the dielectric film **12** is provided, for example, to protect the surface of the piezoelectric substrate **10** on which the IDT electrode **11** is provided, and to improve the voltage resistance and the frequency-temperature characteristics of the surface acoustic wave device **1**. It is noted that when improvement of the frequency-temperature characteristics is attempted, the dielectric film **12** is preferably made of a material having a TCF of which the sign, or polarity is different from that of the piezoelectric substrate **10** or a material having a TCF of which the sign is the same as that of the piezoelectric substrate **10** and of which the absolute value is lower than that of the piezoelectric substrate **10**. For example, when the piezoelectric substrate **10** is preferably made of a material having a negative TCF such as LiNbO₃ or LiTaO₃, the dielectric film **12** is preferably made of silicon oxide such as SiO₂, silicon nitride such as SiN, or the like.

The thickness of the dielectric film **12** is not particularly limited as long as it is such a thickness that an elastic wave excited by the IDT electrode **11** is a surface acoustic wave. The thickness of the dielectric film **12** can be, for example, about 0.01λ to about 0.3λ (λ is the wavelength of the surface acoustic wave).

In addition, the dielectric film **12** may be a laminate of a plurality of dielectric films. For example, the dielectric film **12** may be a laminate of a silicon oxide film and a silicon nitride film.

The method of forming the dielectric film **12** is not particularly limited. The dielectric film **12** can be formed by an appropriate film formation method such as sputtering or CVD (Chemical Vapor Deposition).

As shown in FIG. **2**, in the present preferred embodiment, the IDT electrode **11** is preferably a laminate of a first electrode layer **11a** and a second electrode layer **11b**. Each of the first and second electrode layers **11a** and **11b** can be made of an appropriate conductive material. Each of the first and second electrode layers **11a** and **11b** can be made of, for example, a metal selected from the group consisting of Al, Pt, Au, Ag, Cu, Ti, Ni, and Pd or an alloy including one or more metals selected from the group consisting of Al, Pt, Au, Ag, Cu, Ti, Ni, and Pd. In addition, each of the first and second

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electrode layers **11a** and **11b** may be a laminate of a plurality of conductive layers each formed from the above metal or alloy. The first and second electrode layers **11a** and **11b** may be made of the same material or different materials.

The first electrode layer **11a** is located in a groove **10a** provided in the surface of the piezoelectric substrate **10**. The first electrode layer **11a** is tapered toward the piezoelectric substrate **10** side. Specifically, the first electrode layer **11a** preferably has a trapezoidal shape in cross section. Thus, for example, as compared to the case where the first electrode layer **11a** preferably has a rectangular or substantially rectangular shape in cross section, a gap is unlikely to be formed between the piezoelectric substrate **10** and the first electrode layer **11a**. Therefore, for example, scattering of surface acoustic waves can be effectively prevented.

The ratio (B/R) of the length B of an upper base of the first electrode layer **11a** to the length R of a lower base thereof is, for example, preferably about 0.5 to about 0.98, more preferably about 0.56 to about 0.98, and even more preferably about 0.7 to about 0.95. If the ratio (B/R) is too high, a gap may occur between a side surface of the groove **10a** and the first electrode layer **11a**. If the ratio (B/R) is too low, the cross-sectional area of each electrode finger constituting the IDT electrode **11** is made small and thus the resistance of each electrode finger may be increased. The ratio (HB/R) of the height HB of the first electrode layer **11a** to the length R of the lower base thereof is, for example, preferably about 0.02 to about 0.3 and more preferably about 0.02 to about 0.25. If the ratio (HB/R) is too high, it may be difficult to form the groove **10a**. If the ratio (HB/R) is too low, the effect of embedding a portion of the IDT electrode **11** in the groove **10a** may not be obtained.

The second electrode layer **11b** is provided on the first electrode layer **11a**. The second electrode layer **11b** is located outside the groove **10a**. The second electrode layer **11b** is tapered toward a side opposite to the piezoelectric substrate **10**. Specifically, the second electrode layer **11b** preferably has a trapezoidal shape in cross section.

The length of a lower base of the second electrode layer **11b** preferably is equal or substantially equal to the length of the lower base of the first electrode layer **11a** and is R. The ratio (T/R) of the length T of an upper base of the second electrode layer **11b** to the length of the lower base R thereof is, for example, preferably about 0.8 to about 0.99 and more preferably about 0.86 to about 0.98. If the ratio (T/R) is too high, a gap may occur between the second electrode layer **11b** and the dielectric film **12**. If the ratio (T/R) is too low, the cross-sectional area of each electrode finger constituting the IDT electrode **11** is made small and thus the resistance of each electrode finger may be excessively increased. The ratio (HT/R) of the height HT of the second electrode layer **11b** to the length R of the lower base thereof is preferably about 0.1 to about 0.25 and more preferably about 0.1 to about 0.24, for example. If the ratio (HT/R) is too high, it may be difficult to form the IDT electrode **11**. If the ratio (HT/R) is too low, the resistance of the IDT electrode **11** may be increased.

It is noted that the IDT electrode **11** configured as described above can be formed by sputtering, CVD, or the like using a resist mask.

Meanwhile, as shown in FIG. **4**, when, in an IDT electrode **111**, a second electrode layer **111b** is not tapered toward a side opposite to a piezoelectric substrate and a cross-sectional shape of the second electrode layer **111b** is rectangular or substantially rectangular, a gap **100** may be formed between the second electrode layer **111b** and a dielectric layer **112**.

In contrary, in the present preferred embodiment, the portion of the IDT electrode **11** which is located outside the

groove 10a, namely, the second electrode layer 11b, preferably has a shape that is tapered toward the side opposite to the piezoelectric substrate 10. Thus, the vertex angles of the second electrode layer 11b are larger than 90°, and hence a gap is unlikely to be formed between the second electrode layer 11b and the dielectric film 12. Therefore, scattering of surface acoustic waves can be prevented. In addition, the effect of improving the voltage resistance and the frequency-temperature characteristics by forming the dielectric film 12 can be sufficiently obtained. As a result, high-quality resonant characteristics of the surface acoustic wave device 1 can be achieved.

Experimental Examples

Surface acoustic wave devices having different IDT electrode dimensions as shown in Table 1 below were produced by causing exposure conditions at a resist mask formation for forming an IDT electrode to be variously different from each other. As a result of observing cross sections of the produced surface acoustic wave devices with a scanning electron microscope (SEM), a surface acoustic wave device in which no gap was observed between the IDT electrode and the dielectric film was evaluated as “G”, and a surface acoustic wave device in which a gap was observed between the IDT electrode and the dielectric film was evaluated as “NG”.

TABLE 1

Experimental Example	R	B	T	HT	HB	T/R	HT/R	Result
1	0.5	0.48	0.43	0.12	0.03	0.86	0.24	G
2	0.5	0.29	0.43	0.12	0.15	0.86	0.24	G
3	0.5	0.34	0.44	0.08	0.10	0.88	0.16	G
4	0.5	0.38	0.46	0.10	0.10	0.92	0.2	G
5	0.5	0.49	0.46	0.12	0.01	0.92	0.24	G
6	0.5	0.49	0.47	0.08	0.01	0.94	0.16	G
7	0.5	0.50	0.47	0.08	0.01	0.94	0.16	G
8	0.5	0.47	0.47	0.08	0.03	0.94	0.16	G
9	0.5	0.38	0.47	0.08	0.03	0.94	0.16	G
10	0.5	0.41	0.47	0.08	0.05	0.94	0.16	G
11	0.5	0.50	0.47	0.08	0.05	0.94	0.16	G
12	0.5	0.48	0.48	0.05	0.01	0.96	0.1	G
13	0.5	0.35	0.48	0.05	0.10	0.96	0.1	G
14	0.5	0.28	0.49	0.05	0.15	0.98	0.1	G
15	0.5	0.49	0.50	0.08	0.01	1	0.16	NG
16	0.5	0.50	0.50	0.08	0.03	1	0.16	NG
17	0.5	0.28	0.50	0.10	0.10	1	0.2	NG
18	0.5	0.50	0.50	0.10	0.10	1	0.2	NG

As is clear from the result shown in the above Table 1, it appears that when T/R is made less than 1, formation of a gap between the IDT electrode and the dielectric film can be prevented.

Hereinafter, a modification of the preferred embodiment described above will be described. It is noted that in the

following description, the members having functions substantially common to those in the preferred embodiment described above are designated by the common signs, and the description thereof is omitted.

First Modification

FIG. 3 is a schematic cross-sectional view of a surface acoustic wave device according to a first modification of a preferred embodiment of the present invention.

In the preferred embodiment described above, the case has been described where the IDT electrode 11 preferably includes the laminate of the first and second electrode layers 11a and 11b. However, the present invention is not limited to this configuration. For example, as shown in FIG. 3, the IDT electrode 11 may be composed of a single conductive layer.

While preferred embodiments of the present invention have been described above, it is to be understood that variations and modifications will be apparent to those skilled in the art without departing from the scope and spirit of the present invention. The scope of the present invention, therefore, is to be determined solely by the following claims.

What is claimed is:

1. A surface acoustic wave device comprising:

a piezoelectric substrate including a groove located in a surface thereof;

an IDT electrode including a first electrode layer located in the groove and a second electrode layer located outside the groove; and

a dielectric film arranged on the piezoelectric substrate so as to cover the IDT electrode; wherein

the second electrode layer is tapered toward a side opposite to the piezoelectric substrate, and

a cross-sectional shape of the second electrode layer is trapezoidal, and a ratio T/R of a length T of an upper base to a length R of a lower base in a cross section of the second electrode layer is within a range of about 0.86 to about 0.98.

2. The surface acoustic wave device according to claim 1, wherein the first electrode layer is tapered toward the piezoelectric substrate side.

3. The surface acoustic wave device according to claim 1, wherein a ratio HT/R of a height HT to the length R of the lower base in the cross section of the second electrode layer is within a range of about 0.1 to about 0.25.

4. The surface acoustic wave device according to claim 2, wherein a ratio HT/R of a height HT to the length R of the lower base in the cross section of the second electrode layer is within a range of about 0.1 to about 0.25.

5. The surface acoustic wave device according to claim 1, wherein the dielectric film is made of silicon oxide or silicon nitride.

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